

#### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-600	mA

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

#### ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

# **Thermal Characteristics and Derating Information**

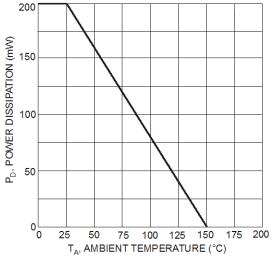


Fig. 1 Max Power Dissipation vs. Ambient Temperature

<sup>6.</sup> For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

<sup>7.</sup> Refer to JEDEC specification JESD22-A114 and JESD22-A115.



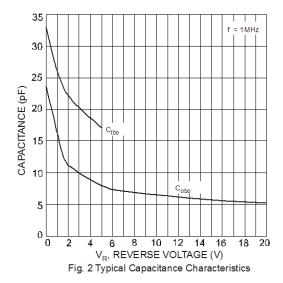
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

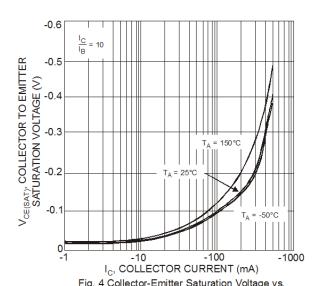
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-60	—	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-60		V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5	_	V	$I_E = -10\mu A, I_C = 0$
Collector Base Cutoff Current	I <sub>CBO</sub>	_	-10	nΑ μΑ	V <sub>CB</sub> = -50V, I <sub>E</sub> = 0 V <sub>CB</sub> = -50V, I <sub>E</sub> = 0, T <sub>A</sub> = +125°C
Collector Cutoff Current	I <sub>CEX</sub>	_	-50	nA	$V_{CE} = -30V, V_{EB(OF F)} = -0.5V$
Base Cutoff Current	I <sub>BL</sub>	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$
ON CHARACTERISTICS (Note 8)					
DC Current Gain	h <sub>FE</sub>	75 100 100 100 50		_	$I_{C} = -100\mu A, \ V_{CE} = -10V$ $I_{C} = -1mA, \ V_{CE} = -10V$ $I_{C} = -10mA, \ V_{CE} = -10V$ $I_{C} = -150mA, \ V_{CE} = -10V$ $I_{C} = -500mA, \ V_{CE} = -10V$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	-0.4 -1.6	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$ $I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		1.3 2.6	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$ $I_C = -500 \text{mA}, I_B = -50 \text{mA}$
SMALL SIGNAL CHARACTERISTICS				•	
Output Capacitance	C <sub>obo</sub>		8	рF	$V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	C <sub>ibo</sub>		30	pF	$V_{EB} = -2V$ , $f = 1.0MHz$ , $I_{C} = 0$
Current Gain-Bandwidth Product	f⊤	200	_	MHz	$V_{CE} = -20V$ , $I_{C} = -50mA$ , $f = 100MHz$
SWITCHING CHARACTERISTICS					
Turn-On Time	ton	_	45	ns	V <sub>CC</sub> = -30V, I <sub>C</sub> = -150mA,
Delay Time	t <sub>d</sub>	_	10	ns	$V_{CC} = -30V, I_{C} = -150IIIA,$ $I_{B1} = -15mA$
Rise Time	t <sub>r</sub>	_	40	ns	IBI - TOHIA
Turn-Off Time	t <sub>off</sub>	_	100	ns	\\\a= 6\\ \  \  \  \  \  \  \  \  \  \  \  \  \
Storage Time	ts	_	80	ns	$V_{CC} = -6V, I_C = -150mA,$ $I_{B1} = I_{B2} = -15mA$
Fall Time	t <sub>f</sub>	_	30	ns	IB1 - IB2 = - IOIIIA

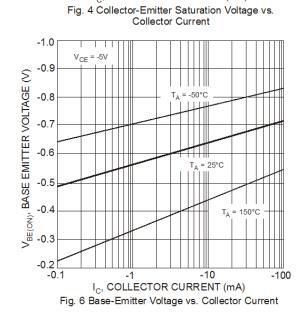
Note: 8. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







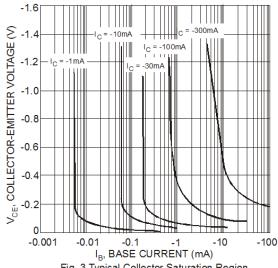


Fig. 3 Typical Collector Saturation Region

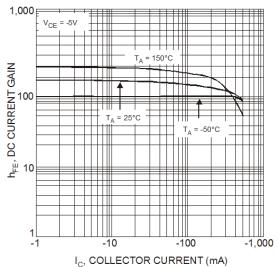


Fig. 5 DC Current Gain vs. Collector Current

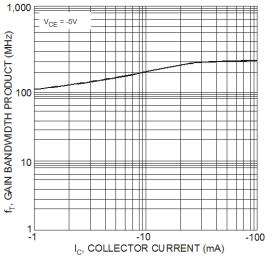
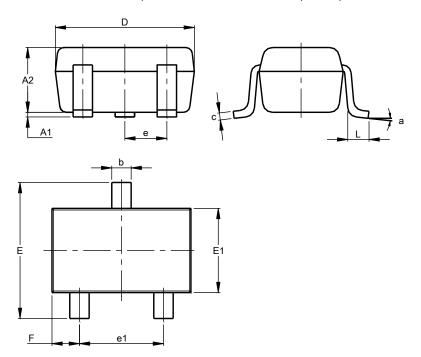


Fig. 7 Gain Bandwidth Product vs. Collector Current



# **Package Outline Dimensions**

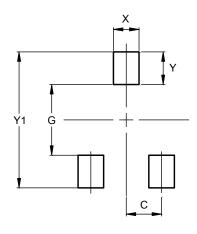
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT323				
Dim	Min	Max	Тур	
A1	0.00	0.10	0.05	
A2	0.90	1.00	0.95	
b	0.25	0.40	0.30	
С	0.10	0.18	0.11	
D	1.80	2.20	2.15	
Е	2.00	2.20	2.10	
E1	1.15	1.35	1.30	
е	0.650 BSC			
e1	1.20	1.40	1.30	
F	0.375	0.475	0.425	
L	0.25	0.40	0.30	
а	8°			
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
G	1.300		
Х	0.470		
Υ	0.600		
Y1	2.500		



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